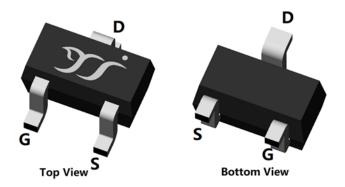
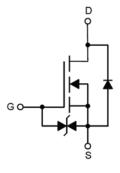




## N-Channel Enhancement Mode Field Effect Transistor



SOT-523



#### **Product Summary**

 $\begin{array}{lll} \bullet \ V_{DS} & 60V \\ \bullet \ I_D & 300mA \\ \bullet \ R_{DS(ON)}(\ at\ V_{GS} = 10V) & <2.5ohm \\ \bullet \ R_{DS(ON)}(\ at\ V_{GS} = 4.5V) & <3.0ohm \\ \bullet \ Gate-Source\ ESD\ Rating\ Up\ to\ 2KV\ (HBM) \end{array}$ 

#### **General Description**

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### **Applications**

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

■ **Absolute Maximum Ratings** (T<sub>A</sub>=25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-source Voltage		$V_{DS}$	60	V	
Gate-source Voltage		$V_{GS}$	±20	V	
Drain Current	T <sub>A</sub> =25°C @ Steady State	_	300	mA	
	T <sub>A</sub> =70 °C @ Steady State	I <sub>D</sub>	240		
Pulsed Drain Current <sup>A</sup>		I <sub>DM</sub>	1.5	А	
Total Power Dissipation @ T <sub>A</sub> =25℃		$P_D$	300	mW	
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>		R <sub>eJA</sub>	416	°C/W	
Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55∼+150	$^{\circ}$	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
2N7002KCE	F2	72C	3000	30000	120000	7" reel



## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units	
Static Parameter							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V	
Zero Gate Voltage Drain Current	ero Gate Voltage Drain Current I <sub>DSS</sub> V <sub>DS</sub> =60V,V <sub>GS</sub> =0V				1	μΑ	
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ = $\pm 20$ V, $V_{DS}$ =0V			±10	μΑ	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}$ = $V_{GS}$ , $I_D$ =250 $\mu$ A	1	1.5	2.5	V	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =300mA		1.9	2.5		
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =200mA		2.0	3.0	Ω	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =300mA,V <sub>GS</sub> =0V			1.2	V	
Maximum Body-Diode Continuous Current	Is				300	mA	
Dynamic Parameters							
Input Capacitance	C <sub>iss</sub>			27		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V, $f$ =1MHZ		3			
Reverse Transfer Capacitance	C <sub>rss</sub>			2			
Switching Parameters							
Total Gate Charge	$Q_g$	V <sub>GS</sub> =10V,V <sub>DS</sub> =30V,I <sub>D</sub> =0.3A		1.65	2.4	nC	
Turn-on Delay Time	t <sub>D(on)</sub>	$V_{GS}$ =10V, $V_{DD}$ =30V, $I_{D}$ =300mA,		6.5		- ns	
Turn-off Delay Time	$t_{D(off)}$	$R_{\text{GEN}}=6\Omega$		9.6			
Reverse recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =300mA,V <sub>R</sub> =25V, di/dt=- 100A/μs		24		ns	

A. Pulse Test: Pulse Width  $\leq$  300us, Duty cycle  $\leq$  2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.





#### **■ Typical Performance Characteristics**

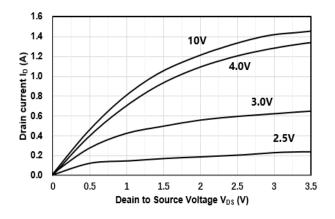


Figure 1. Output Characteristics

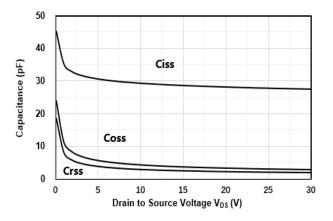


Figure 3. Capacitance Characteristics

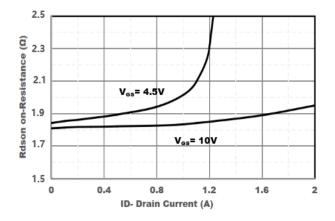


Figure 5. Drain-Source on Resistance

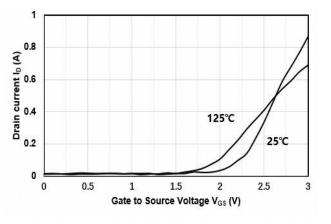


Figure 2. Transfer Characteristics

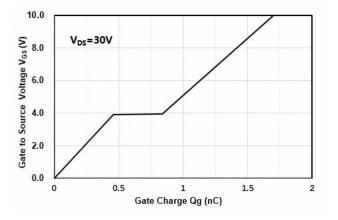


Figure 4. Gate Charge

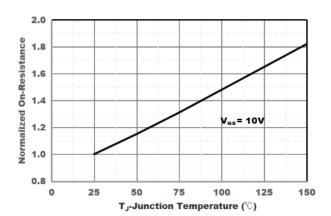


Figure 6. Drain-Source on Resistance



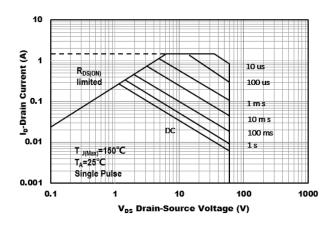


Figure 7. Safe Operation Area

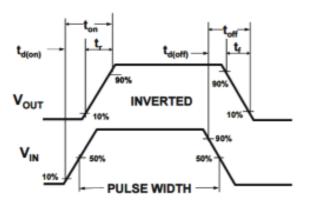
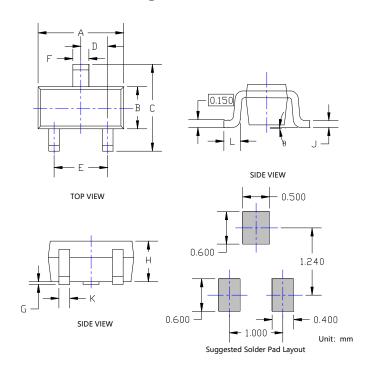


Figure8. Switching wave



# ■ SOT-523 Package Information



	DIMENSIONS				
SYMBOL	INC	HES	Millimeter		
	MIN.	MAX.	MIN.	MAX.	
Α	0.059	0.067	1.500	1.700	
В	0.030	0.033	0.750	0.850	
С	0.057	0.069	1.450	1.750	
D	0.020TYP		0.500TYP		
E	0.035	0.043	0.900	1.100	
F	0.010	0.018	0.250	0.450	
G	0.000	0.004	0.000	0.100	
Н	0.024	0.031	0.600	0.800	
J	0.004	0.008	0.100	0.200	
К	0.006	0.014	0.150	0.350	
L	0.010	0.018	0.260	0.460	
θ	0°	8°	0.	8°	

- NOTE: 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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